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PATENT APPLICATION

SEP 12 2002
TECHNOLOGY CENTER 2600

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Docket No: Q65781

Hiroyuki NAGASAWA

Appln. No.: 09/924,872

Group Art Unit: 2812

Confirmation No.: 3695

Examiner: S. MULPURI

Filed: August 09, 2001

For: SILICON CARBIDE AND METHOD OF MANUFACTURING THE SAME

EXCESS CLAIM FEE PAYMENT LETTER

Commissioner for Patents
Washington, D.C. 20231

Sir:

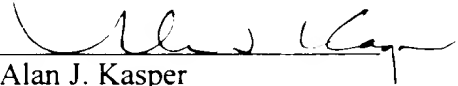
An Amendment Under 37 C.F.R. § 1.111 is attached hereto for concurrent filing in the above-identified application. The resulting excess claim fee has been calculated as shown below:

	After Amendment		Highest No. Previously Paid For					
Independent	4	-	3	=	1	X	\$84.00	= \$84.00
TOTAL								= \$84.00

A check for the statutory fee of \$84.00 is attached. The USPTO is directed and authorized to charge all required fees, except for the Issue Fee and the Publication Fee, to Deposit Account No. 19-4880. Please also credit any overpayments to said Deposit Account. A duplicate copy of this letter is enclosed.

Respectfully submitted,

SUGHRUE MION, PLLC
2100 Pennsylvania Avenue, N.W.
Washington, D.C. 20037-3213
Telephone: (202) 293-7060
Facsimile: (202) 293-7860
Date: September 4, 2002


Alan J. Kasper
Registration No. 25,426



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TECHNICAL CENTER 4000

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated June 4, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please enter the following amended claim:

15. (Amended) A semiconductor device comprising a silicon carbide layer, said silicon carbide being manufactured by the method comprising:

depositing silicon from a vapor phase or a liquid phase onto a substrate and forming a silicon layer on the substrate;

doping the silicon layer with an impurity composed of at least one element selected from a group consisting of N, B, Al, Ga, In, P, As, Sb, Se, Zn, O, Au, V, Er, Ge, and Fe, to form a doped silicon layer; and

carbonizing the doped silicon layer into a silicon carbide layer of the silicon carbide doped with the impurity.